

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)		ATTY. DOCKET NO. 57810-084		SERIAL NO. Divisional of Appl No. 10/084,050 <i>10/796154</i>				
		APPLICANT Nobuhiko HAYASHI, et al.						
		FILING DATE March 10, 2004		GROUP 2818				
U.S. PATENT DOCUMENTS								
EXAMINER'S INITIALS	CITE NO.	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		Number-Kind Code(s) (if known)						
<i>DL</i>		US	6,015,979	1/18/2000	Sugiura et al.			
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		Country Code(s) - Number - Kind Code(s) (if known)					Yes	No
<i>DL</i>			2000-164989	6/16/2000			Japan (w/ English Abstract)	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
<i>DL</i>		S. Nakamura et al., "Long lifetime violet InGaIn/GaN/AlGaIn-based semiconductor lasers", Journal of Oyo Denshi Bussei Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.						
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.						
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EXAMINER				DATE CONSIDERED				
<i>DL</i>				<i>OCT - 2005</i>				

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